

Supporting information

**Bi-continuous network structure of *p*-DTS(FBTTh₂)₂ /EP-PDI
via selective solvent vapor annealing**

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Figure captions

Figure S1. The photographs of *p*-DTS(FBTTh₂)₂ (1, 2, 3) and EP-PDI (4, 5, 6) solutions prepared by different solvents (1mg/mL).

Fig.S2 UV-Vis absorption spectra of pure *p*-DTS(FBTTh₂)₂ and EP-PDI films prepared from chloroform solutions.

Figure S3. Ex-situ GIXD of *p*-DTS(FBTTh₂)₂:EP-PDI blend films after (a) ODCB-SVA and (b) EA-SVA treatments.

Figure S4. Photocurrent-voltage curves for hole-only devices of as deposited, CB-SVA treated and TA treated *p*-DTS(FBTTh₂)₂:EP-PDI blend films.

Figure S1.

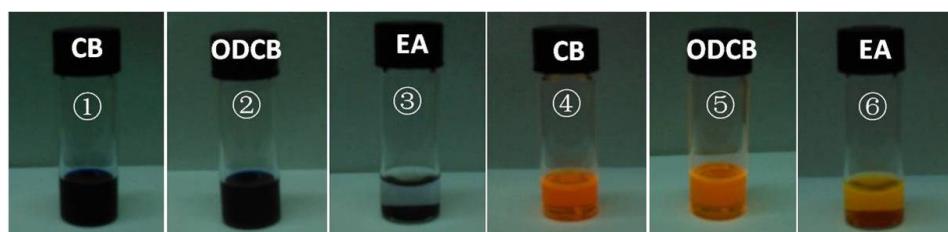


Figure S2.

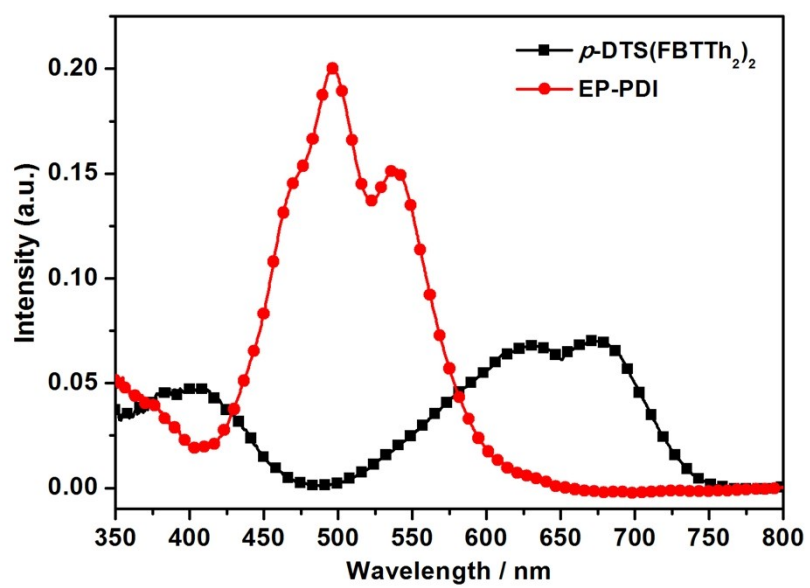


Figure S3.

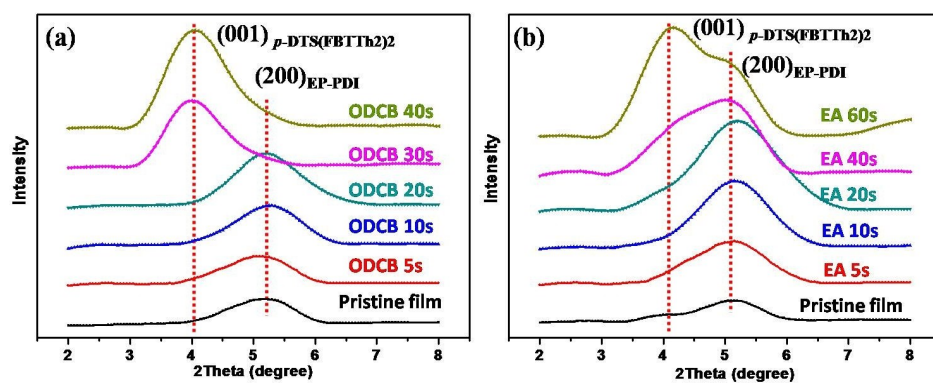


Figure S4.

